2SD1011

Silicon NPN epitaxial planer type

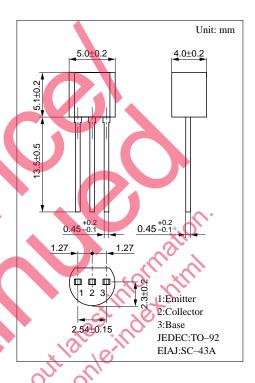
For low-frequency amplification

Features

- High foward current transfer ratio h_{FE}.
- ullet Low collector to emitter saturation voltage $V_{\text{CE(sat)}}$.
- High emitter to base voltage V_{EBO}.

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	100	V
Collector to emitter voltage	V _{CEO}	100	V
Emitter to base voltage	V _{EBO}	15	V
Peak collector current	I_{CP}	50	mA
Collector current	I_{C}	20	mA
Collector power dissipation	P _C	300	mW
Junction temperature	$T_{\rm j}$	150	°C
Storage temperature	T _{stg}	−55 ~ +150	°C



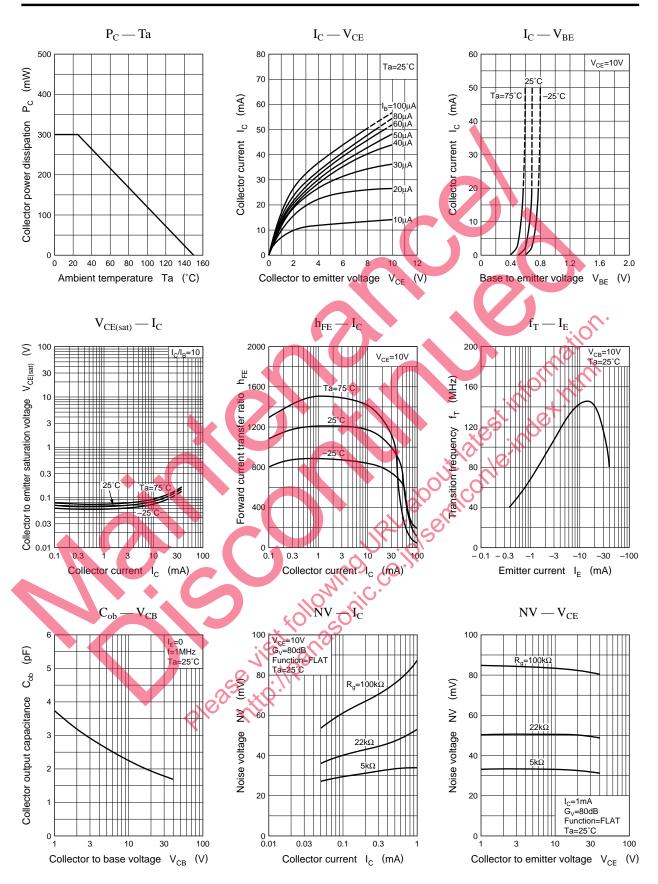
Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 60V, I_{E} = 0$			100	nA
	I_{CEO}	$V_{QE} = 60V, I_{B} = 0$			1	μА
Collector to base voltage	V_{CBO}	$I_{\rm C} = 10 \mu A$, $I_{\rm E} = 0$	100			V
Collector to emitter voltage	V _{CEO}	$I_{\rm C} = 1$ mA, $I_{\rm B} = 0$	100			V
Emitter to base voltage	V _{EBO}	$I_{\rm E} = 10 \mu A, I_{\rm C} = 0$	15			V
Forward current transfer ratio	h _{FE}	$V_{CE} = 10V, I_{C} = 2mA$	400		1200	
Collector to emitter saturation voltage	V _{CE(sat)}	$I_C = 10$ mA, $I_B = 1$ mA		0.05	0.2	V
Transition frequency	f_T	$V_{CB} = 10V, I_E = -2mA, f = 200MHz$		200		MHz
Noise voltage N	NV	$V_{CE} = 10V, I_{C} = 1mA, G_{V} = 80dB$		80		mV
		$R_g = 100k\Omega$, Function = FLAT		80		IIIV

*h_{FE} Rank classification

Rank	R	S		
h_{FE}	400 ~ 800	600 ~ 1200		

Transistor 2SD1011



2 Panasonic

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